

Silicon NPN Power Transistors

2SD1789

DESCRIPTION

- With ITO-220 package
- Switching power transistor

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

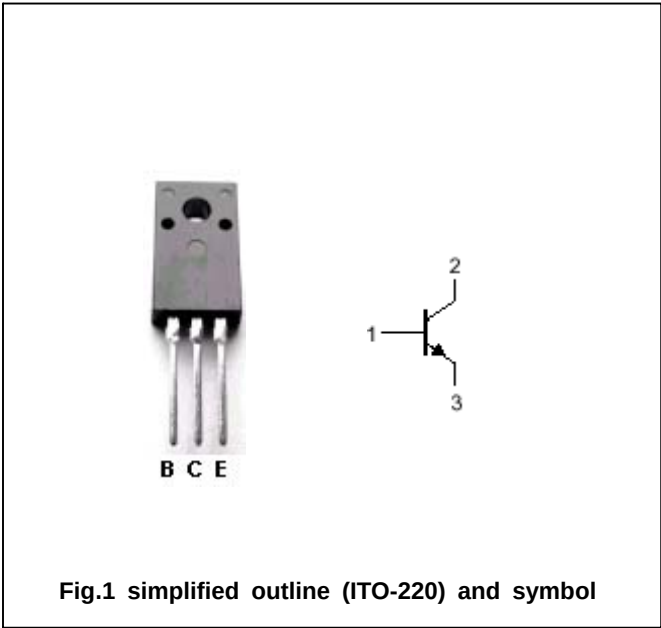


Fig.1 simplified outline (ITO-220) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	200	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		±4	A
I _{CM}	Collector current-Peak		±6	A
I _B	Base current		0.3	A
I _{BM}	Base current-Peak		0.5	A
P _T	Total power dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C
V _{dis}	Dielectric strength	Terminals to case,AC 1 minute	2	kV
TOR	Mounting torque	(Recommended torque:0.3N·m)	0.5	N·m

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-C}	Thermal resistance junction to case	5.0	°C/W

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CHARACTERISTICS

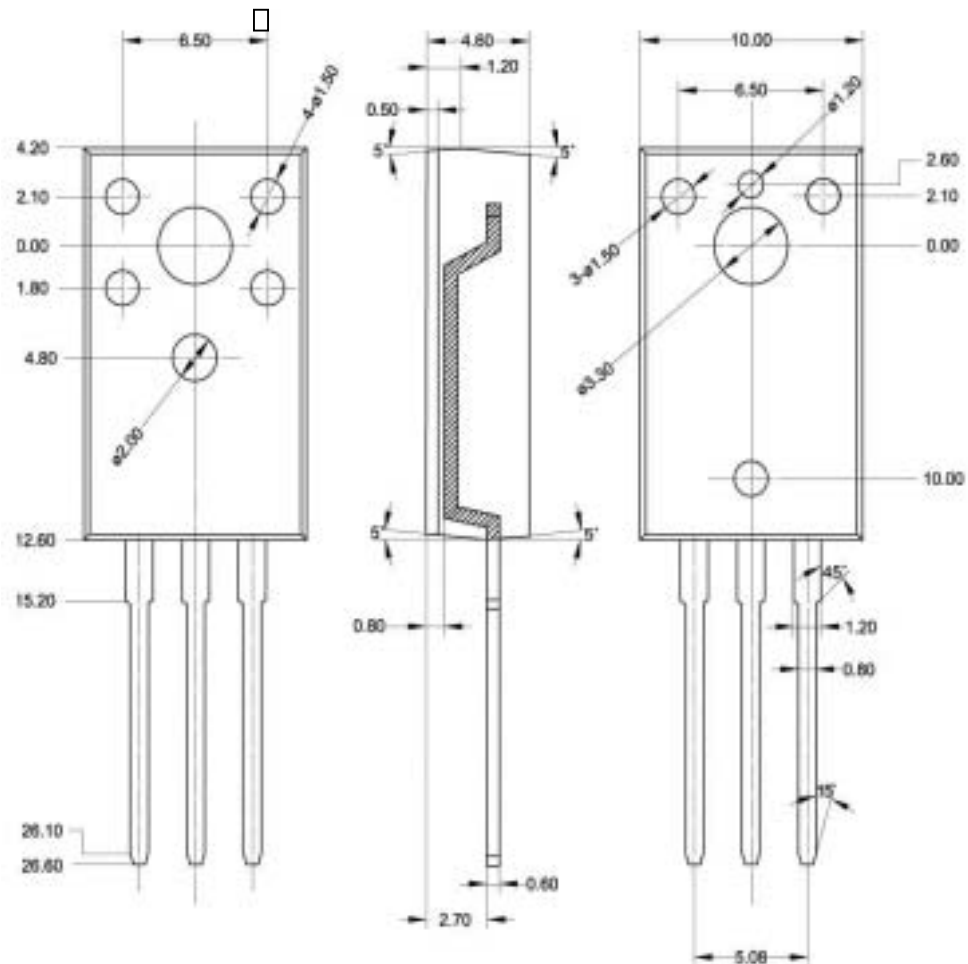
Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=1A; I_B=2mA$			1.5	V
V_{BEsat}	Emitter-base saturation voltage	$I_C=1A; I_B=2mA$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V$			0.1	mA
I_{CEO}	Collector cut-off current	$V_{CE}=200V$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V$			5	mA
h_{FE}	DC current gain	$I_C=1A; V_{CE}=3V$	1500		30000	
f_T	Transition frequency	$I_C=0.4A; V_{CE}=10V$		20		MHz
t_{on}	Turn-on time	$I_C=1A; I_{B1}=I_{B2}=2mA,$ $R_L=25\Omega$ $V_{BB2}=4V$			2.0	μs
t_s	Storage time				12	μs
t_f	Fall time				5.0	μs

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.20 mm)